

### Power Modules - Thyristor/Diode

#### FEATURES

- High surge capability
- Qualified for industrial level
- Thick copper baseplate
- Easy mounting on heatsink
- International standard TO-240AA

#### TYPICAL APPLICATIONS

- Power supplies
- Machine tools control
- High power drives
- Welders
- Medium traction

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}, I_{F(AV)}$		25	A
	$T_{Case}$	85	°C
$I_{T(RMS)}, I_{F(RMS)}$		55	A
	$T_{Case}$	85	°C
$I_{TSM}, I_{FSM}$	50 Hz	570	A
	60 Hz	620	A
$I^2t$	50 Hz	1.48	kA <sup>2</sup> s
	60 Hz	1.61	kA <sup>2</sup> s
$V_{DRM}/V_{RRM}$		200 to 1600	V
$t_q$	Typical	125	µs
$T_J$		-40 to 125	°C

#### ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
SERIES	VOLTAGE CODE	$V_{DRM}/V_{RRM}$ , MAX. RE- PETITIVE PEAK AND OFF-STATE VOLTAGE	$V_{RSM}$ , MAX. NON- REPETITIVE PEAK VOLTAGE (V)	$I_{DRM}/I_{RRM}$ , MAX. at $T_J$ = $T_{J(Max.)}$ (mA)
TD25/...	02	200	300	15
TD25/...	04	400	500	
TD25/...	06	600	700	
TD25/...	08	800	900	
TD25/...	10	1000	1100	
TD25/...	12	1200	1300	
TD25/...	14	1330	1500	
TD25/...	16	1520	1700	

## Power Modules - Thyristor/Diode

MAXIMUM ALLOWABLE RATINGS					
SYMBOL	DESCRIPTION	TEST CONDITIONS		VALUE	UNITS
$I_{T,F(AV)}$	Maximum average on-state current at heatsink temperature	180° conduction, half sine wave		25	A
				85	°C
$I_{T,F(RMS)}$	Maximum RMS on-state current	DC at 25°C heatsink temperature		55	A
$I_{TSM}, I_{FSM}$	Maximum peak, one-cycle non-repetitive surge current	t = 10 ms	100% $V_{RRM}$ reapplied	Sinusoidal half wave, initial $T_J = T_J \text{ max.}$	0.50
		t = 8.3 ms	100% $V_{RRM}$ reapplied		0.54
		t = 10 ms	No voltage reapplied		0.57
		t = 8.3 ms	No voltage reapplied		0.62
$I^2t$	Maximum $I^2t$	t = 10 ms	100% $V_{RRM}$ reapplied		1.30
		t = 8.3 ms	100% $V_{RRM}$ reapplied		1.41
		t = 10 ms	No voltage reapplied		1.48
		t = 8.3 ms	No voltage reapplied		1.61
$I^2t^{1/2}$	Maximum $I^2t^{1/2}$	t = 0.1 to 10 ms, no voltage reapplied		17.7	$\text{kA}^2\text{s}^{1/2}$
$V_{T,F(TO)}$	Low level threshold voltage	(16.7% $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$ ), $T_J = T_J \text{ max.}$		0.95	V
$r_T$	Low level on-state slope resistance			12.60	mΩ
$V_{TM}, V_{FM}$	Maximum on-state voltage	$I_{pk} = 78\text{A}$ , 50Hz half sine pulse, $T_J = T_J \text{ max.}$		2.00	V
$I_H$	Maximum holding current	$T_J = 25^\circ\text{C}$ , anode supply 12V resistive load		200	mA
$I_L$	Typical latching current			400	

SWITCHING					
SYMBOL	DESCRIPTION	TEST CONDITIONS		VALUE	UNITS
dI/dt	Maximum non-repetitive rate of rise of turned-on current	Gate drive 20 V, 20 Ω, $t_r \leq 1 \mu\text{s}$ , $T_J = T_J \text{ max.}$ , anode voltage $\leq 80\%$ $V_{DRM}$		150	A/ $\mu\text{s}$
$t_d$	Typical delay time	Gate current 1 A, $dI_g/dt = 1 \text{ A}/\mu\text{s}$ , $V_d = 0.67\%$ $V_{DRM}$ , $T_J = 25^\circ\text{C}$		0.7	$\mu\text{s}$
$t_q$	Typical turn-off time			125	

BLOCKING					
SYMBOL	DESCRIPTION	TEST CONDITIONS		VALUE	UNITS
dV/dt	Maximum critical rate of rise of off-state voltage	$T_J = T_J \text{ max.}$ Linear to 80% rated $V_{DRM}$		500	V/ $\mu\text{s}$
$I_{RRM}, I_{DRM}$	Maximum peak reverse and off-state leakage current	$T_J = T_J \text{ max.}$ , rated $V_{DRM}/V_{RRM}$ applied		15	mA

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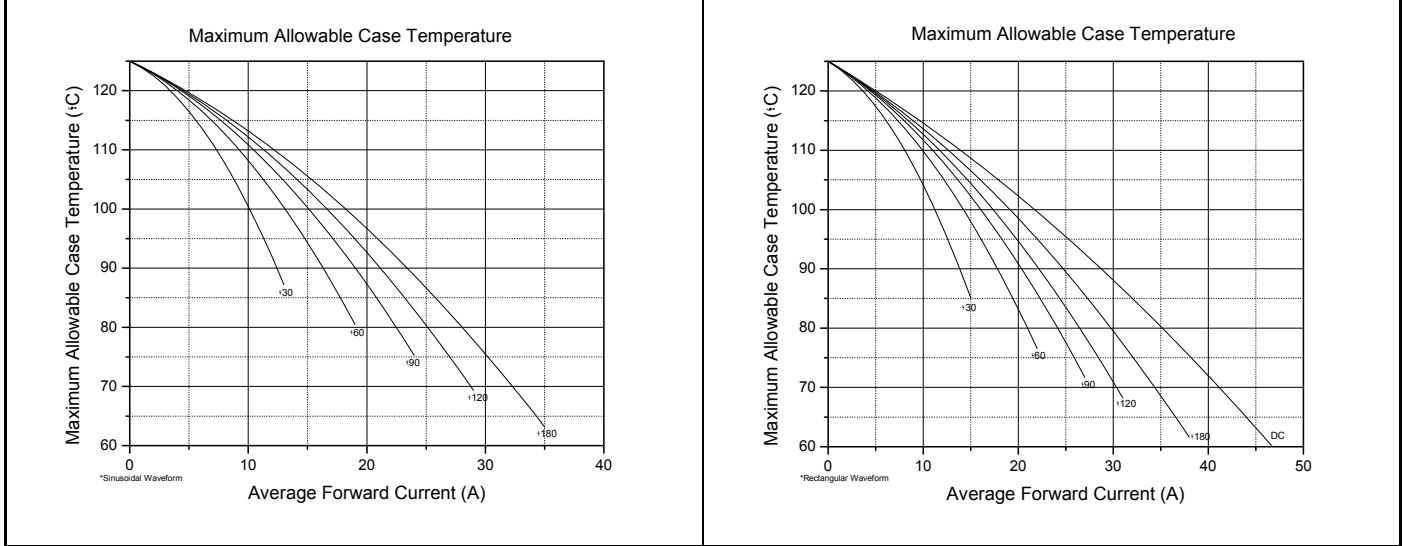
TRIGGERING						
SYMBOL	DESCRIPTION	TEST CONDITIONS	VALUE		UNITS	
			TYP.	MAX.		
$P_{GM}$	Maximum peak gate power	$T_J = T_J \text{ max.}, t_p \leq 5\text{ms}$	10		W	
$P_{G(AV)}$	Maximum average gate power	$T_J = T_J \text{ max.}, f = 50\text{Hz}, d\% = 50$	2.5			
$I_{GM}$	Maximum peak gate current	$T_J = T_J \text{ max.}, t_p \leq 5\text{ms}$	1		A	
$-V_{GM}$	Maximum negative gate voltage	$T_J = T_J \text{ max.}, t_p \leq 5\text{ms}$	2		V	
$I_{GT}$	DC gate current to trigger	$T_J = -40^\circ\text{C}$	Maximum required gate trigger/current/voltage are the lowest values which will trigger all units, 12V anode to cathode applied	-	300	mA
		$T_J = 25^\circ\text{C}$		80	150	
$V_{GT}$	DC gate voltage to trigger	$T_J = -40^\circ\text{C}$		-	4	V
		$T_J = 25^\circ\text{C}$		-	2	
$V_{GD}$	DC gate voltage not to trigger	$T_J = T_J \text{ max.}$	0.2		V	

THERMAL AND MECHANICAL SPECIFICATIONS					
SYMBOL	DESCRIPTION	TEST CONDITIONS	VALUE	UNITS	
$T_J$	Maximum operating junction temperature	-	-40 to 125	°C	
$T_{Stg}$	Maximum storage temperature	-	-40 to 150		
$R_{thJ-hs}$	Maximum thermal resistance, junction to heatsink	DC	0.400	°C/W	
		180° sine wave	0.463		
		120° rectangular wave	0.491		
$R_{thC-hs}$	Maximum thermal resistance, case to heat-sink	Mtg. Surface smooth, flat, greased	0.100		
-	Mounting force, $\pm 10\%$	To terminal (To heatsink)	3(5)	N.m	
-	Approximate weight	-	110	g	
-	Case style	-	TO-240AA	JEDEC	

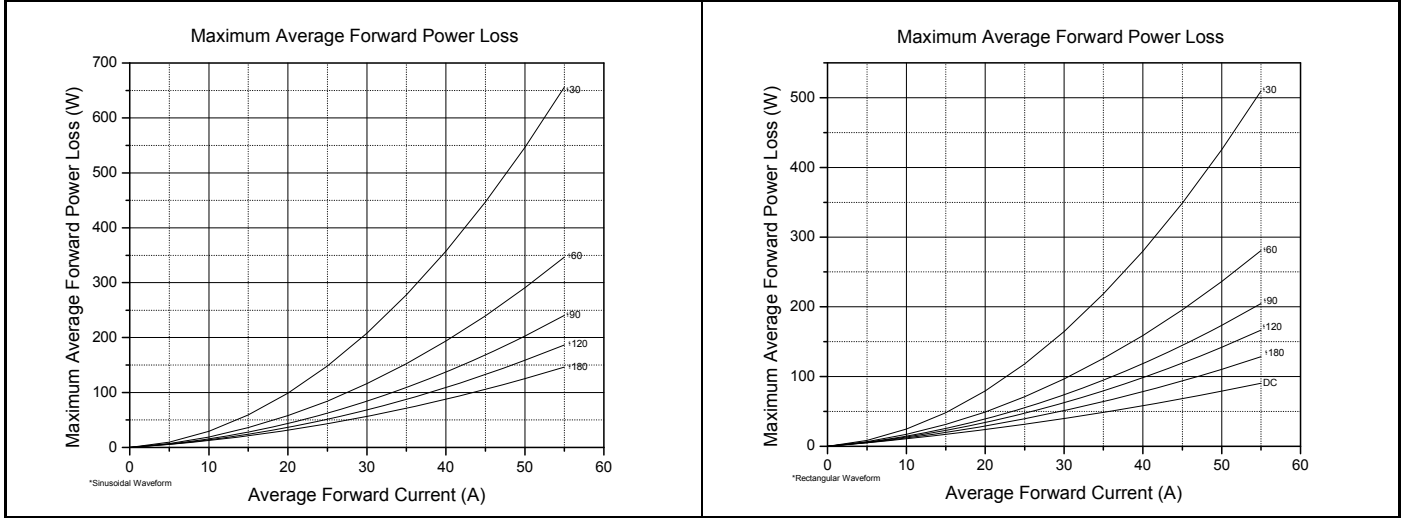
CURRENT FORM FACTOR								
FORM FACTOR	CONDUCTION ANGLE	15°	30°	45°	60°	90°	120°	180°
		Sine wave		31.956	15.832	10.452	7.721	4.933
Rectangular wave		24.000	12.000	8.000	6.000	4.000	3.000	2.000

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#### CURRENT RATINGS CHARACTERISTICS

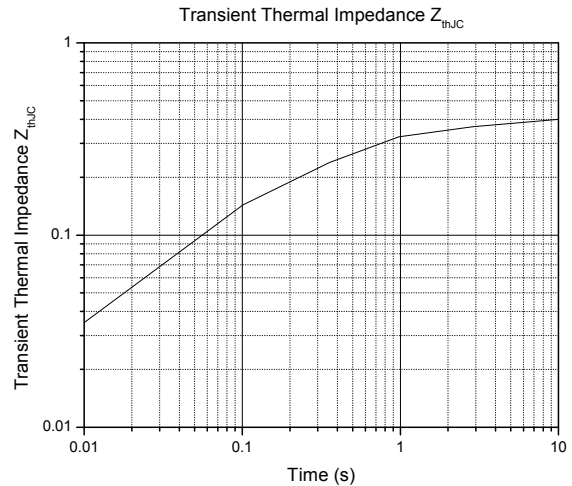
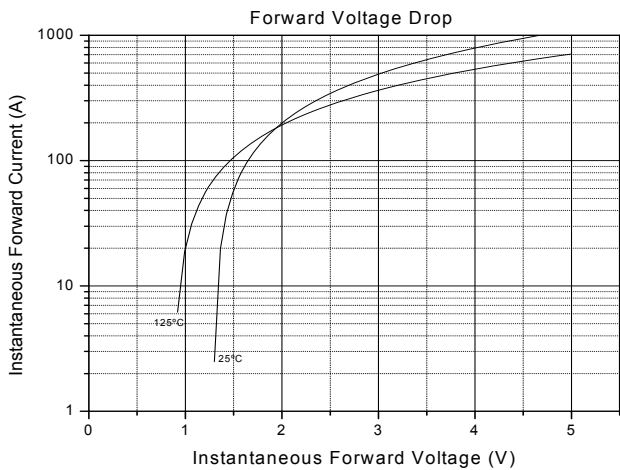


#### ON-STATE POWER LOSS CHARACTERISTICS

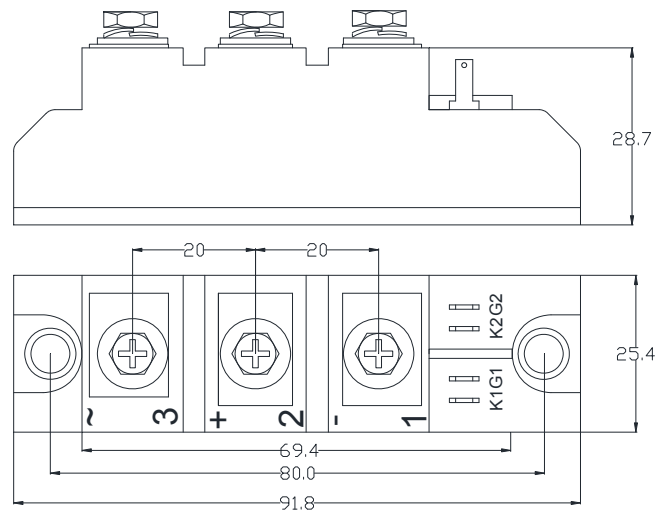
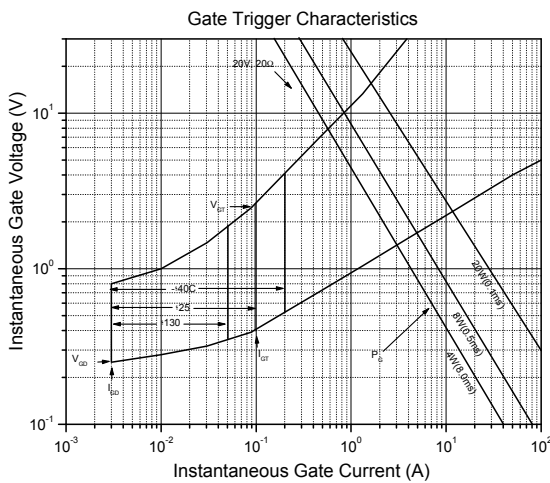


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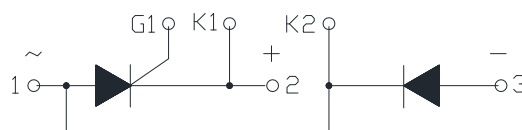
#### FORWARD VOLTAGE DROP / THERMAL IMPEDANCE CHARACTERISTICS



#### GATE TRIGGER / OUTLINE CHARACTERISTICS



#### CIRCUIT CONFIGURATION



### Power Modules - Thyristor/Diode

**ORDERING INFORMATION**

**Device code**

TD	25	/	16	-	-	-
①	②	③	④	⑤	⑥	⑦

1	<ul style="list-style-type: none"> <li>- N = Phase Control Thyristors</li> <li>- F = Fast Thyristors (inverter grade)</li> <li>- D = Normal Recovery Diodes</li> <li>- DF = Fast Recovery Diodes</li> <li>- DD = Module (diode-diode)</li> <li>- DT = Module (diode-thyristor)</li> <li>- TD = Module (thyristor-diode)</li> <li>- TT = Module (thyristor-thyristor)</li> <li>- P = Press-fit diode</li> </ul>
2	- Average Current Code
3	- Essential Part Number
4	- Voltage Code x 100 = $V_{RRM}$
5	<ul style="list-style-type: none"> <li>- Turn-off time (fast thyristors only)</li> <li>- Reverse Recovery Time (fast diodes only)</li> </ul>
6	<ul style="list-style-type: none"> <li>- M = Metric Thread</li> <li>- I = Inch Thread</li> </ul>
7	<ul style="list-style-type: none"> <li>- None = Anode to stud (stud diodes only)</li> <li>- R = Cathode to stud (stud diodes only)</li> </ul>

#### Disclaimer

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